

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	6	US-64932582-\$ DID. OR US-64871082-\$ DID. OR US-5761109-\$ DID. OR US-5903492-\$ DID. OR US-6094370-\$ DID. OR US-632078B1-\$ DID. OR US-64733382-\$ DID.	US-PGPUB ; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/10 12:37
L2	65303	"365"/\$.ccls.	US-PGPUB ; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/10 11:56
L3	571	257/104-106.ccls.	US-PGPUB ; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/10 11:59
L4	116	TAKASHIMA.in. and 2	US-PGPUB ; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/10 12:38
L5	2971225 0	( ferroelectric and memory and device memory and cells and transistor having a source terminal drain terminal and c capacitor between terminals)	US-PGPUB ; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/10 12:43
L6	64959	2 and 5	US-PGPUB ; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/10 12:44
L7	1551	365/145.ccls.	US-PGPUB ; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/10 12:48
L8	15784	7 and source nad drain and ferroelectric with memory	US-PGPUB ; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/10 12:48
L9	765	7 and source and drain and ferroelectric with memory	US-PGPUB ; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/10 12:49
L10	288	9 and "ferroelectric memory device"	US-PGPUB ; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/10 12:50

L11	642	9 and "ferroelectric capacitor"	US-PGPUB ; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/10 12:50
L12	318	9 and "ferroelectric capacitor" with source with drain	US-PGPUB ; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/10 12:50
L13	13147	12 nad "bit line" and "plate line"	US-PGPUB ; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/10 12:51
L14	215	12 and "bit line" and "plate line"	US-PGPUB ; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/10 12:51
L15	146	14 and (potential or voltage) with (higher nad lower)	US-PGPUB ; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/10 12:52
L16	35	15 and (third and fourth) with potential	US-PGPUB ; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/10 13:05

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L7	1551	365/145.ccls.	US-PGPUB ; USPAT; EPO; JPO; DERWENT	OR	ON	2005/03/10 12:44

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